

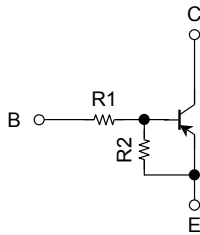
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process) (Bias Resistor Built-in Transistor)

**RN2961FE,RN2962FE,RN2963FE  
RN2964FE,RN2965FE,RN2966FE**

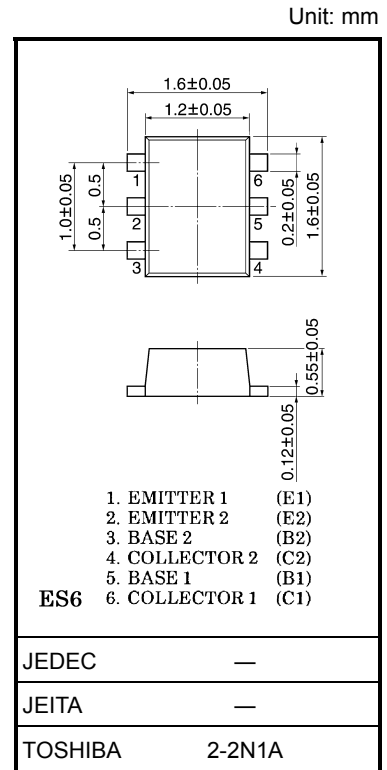
Switching, Inverter Circuit, Interface Circuit and  
Driver Circuit Applications

- Two devices are incorporated into an Extreme-Super-Mini (6-pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enables the manufacture of ever more compact equipment and lowers assembly cost.
- Complementary to RN1961FE~RN1966FE

**Equivalent Circuit and Bias Resistor Values**



Type No.	R1 (kΩ)	R2 (kΩ)
RN2961FE	4.7	4.7
RN2962FE	10	10
RN2963FE	22	22
RN2964FE	47	47
RN2965FE	2.2	47
RN2966FE	4.7	47



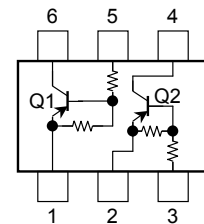
Weight: 0.003 g (typ.)

**Maximum Ratings (Ta = 25°C) (Q1, Q2 common)**

Characteristics		Symbol	Rating	Unit
Collector-base voltage	RN2961FE~2966FE	$V_{CB0}$	-50	V
Collector-emitter voltage		$V_{CEO}$	-50	V
Emitter-base voltage	RN2961FE~2964FE	$V_{EBO}$	-10	V
	RN2965FE, 2966FE		-5	
Collector current	RN2961FE~2966FE	$I_C$	-100	mA
Collector power dissipation		$P_C$ (Note)	100	mW
Junction temperature		$T_j$	150	°C
Storage temperature range		$T_{stg}$	-55~150	°C

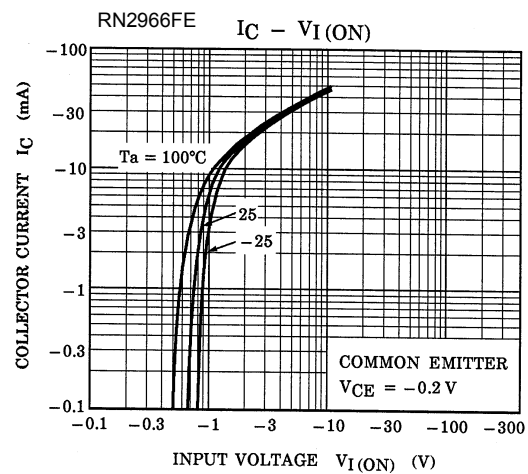
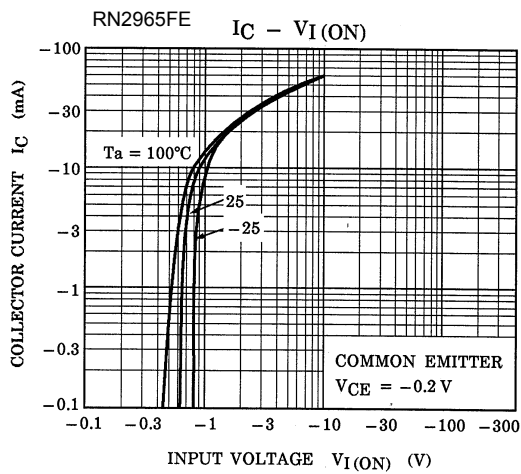
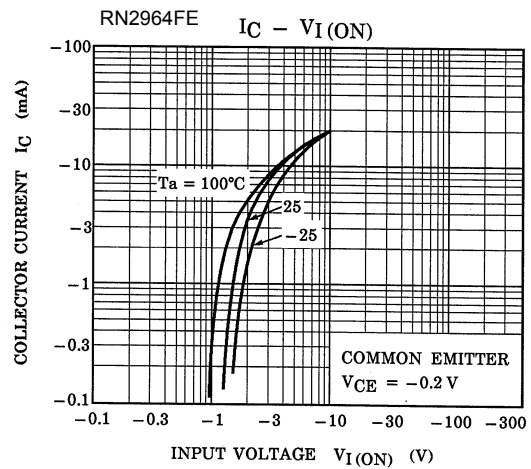
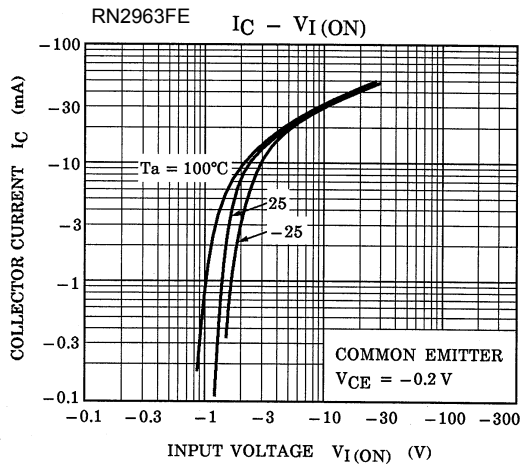
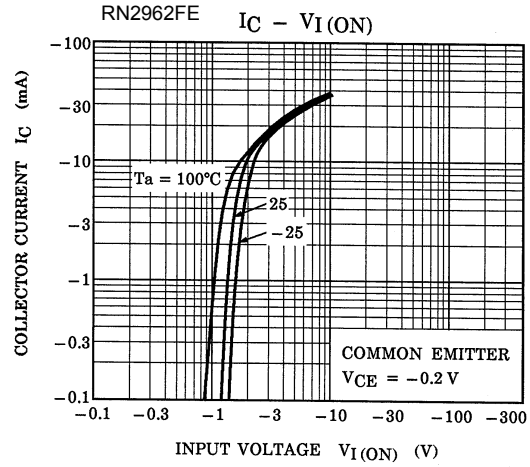
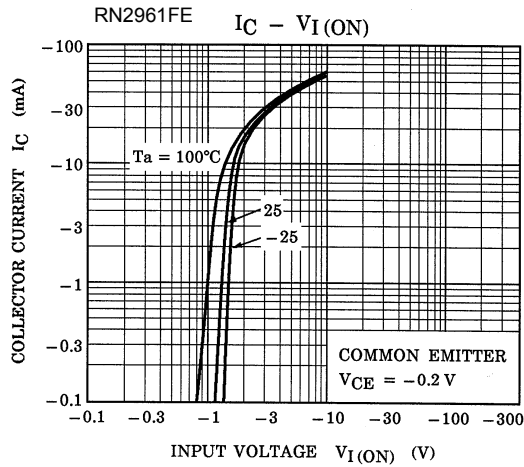
Note: Total rating

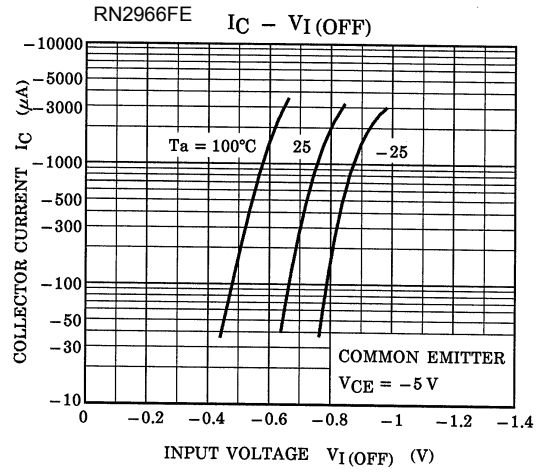
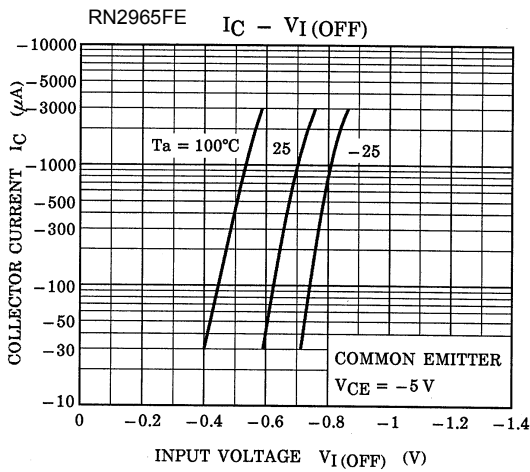
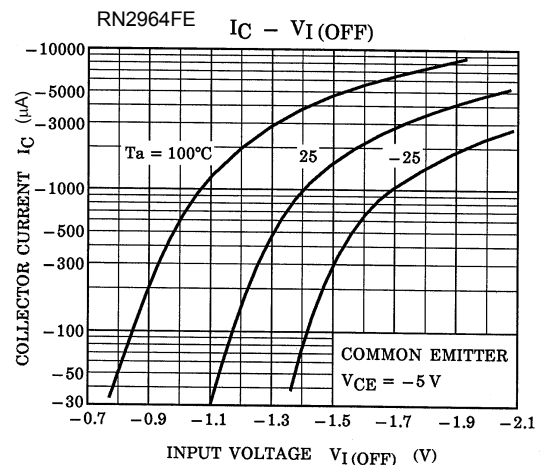
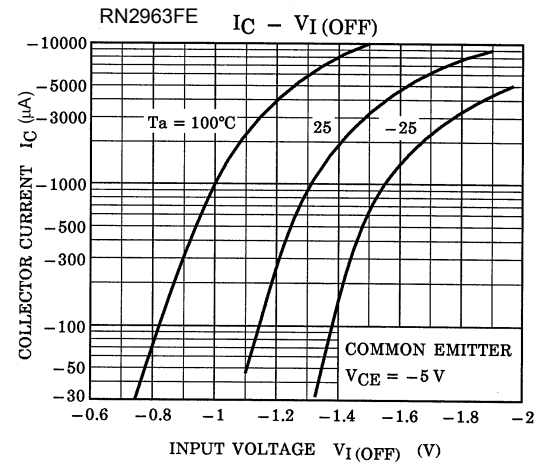
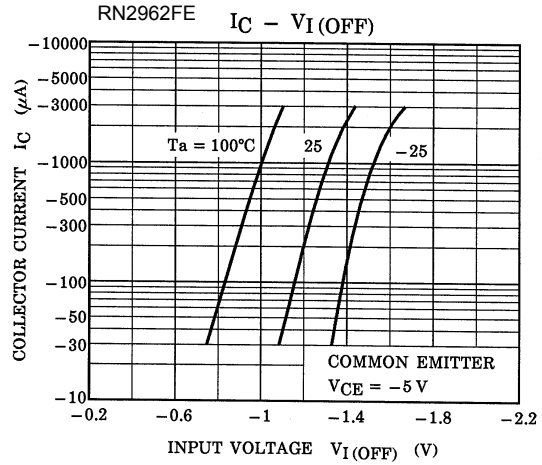
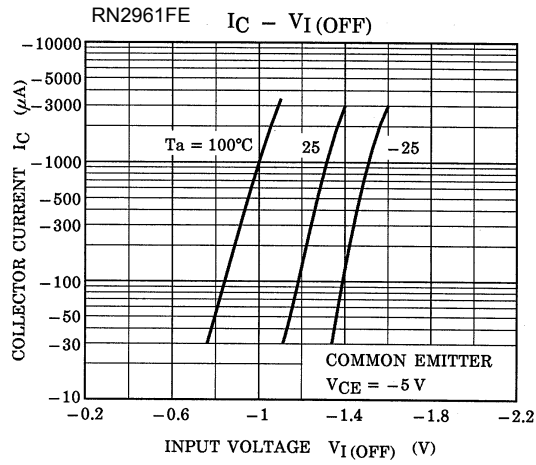
**Equivalent Circuit (top view)**

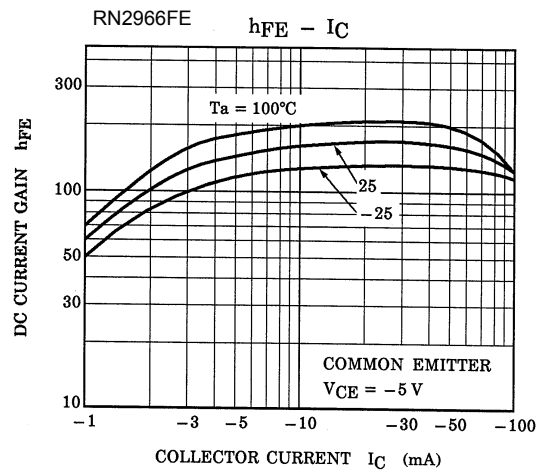
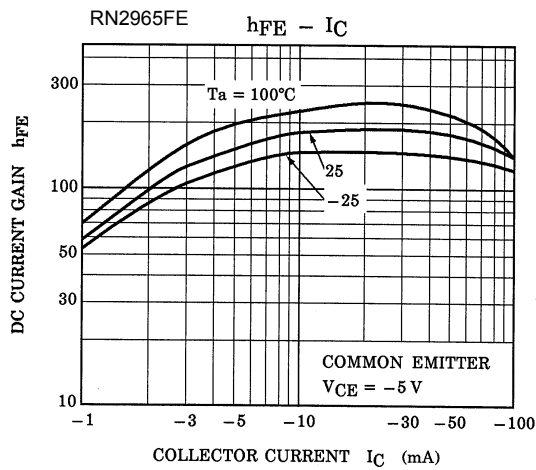
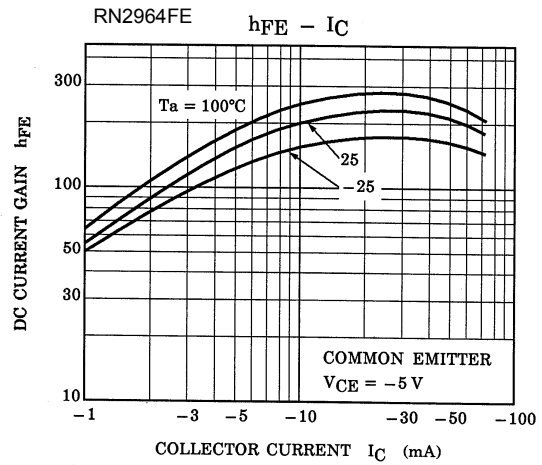
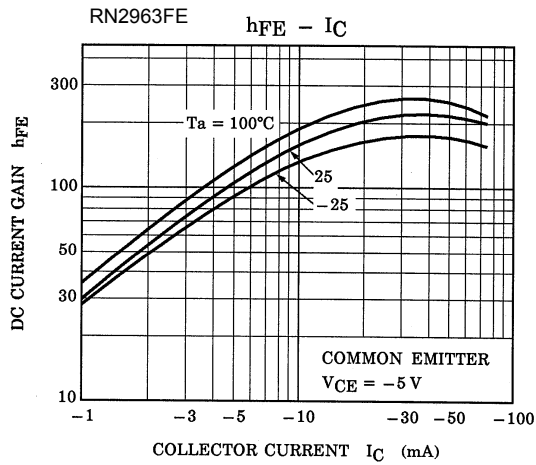
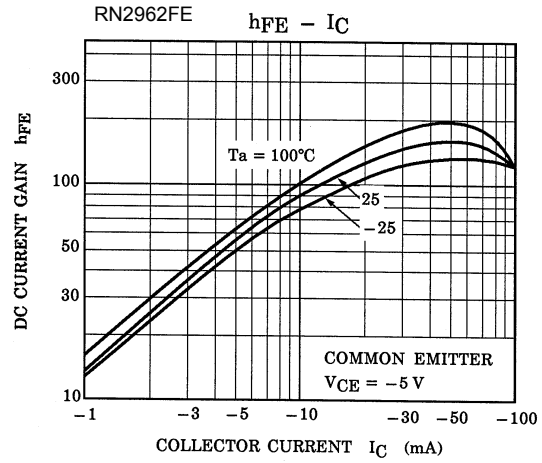
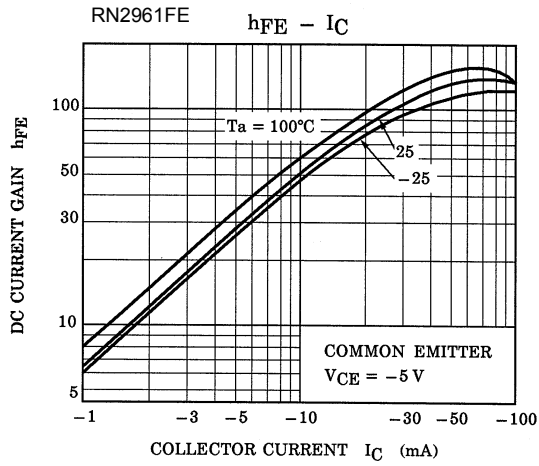


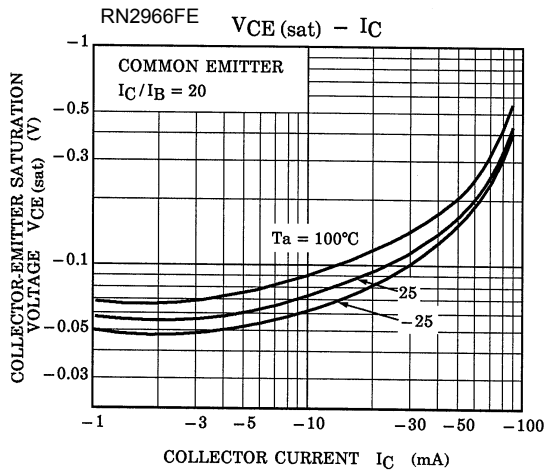
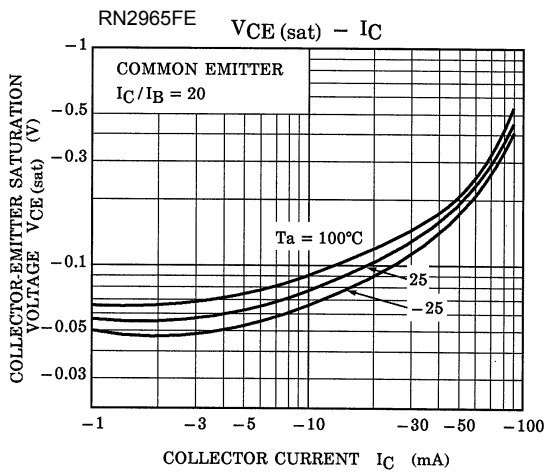
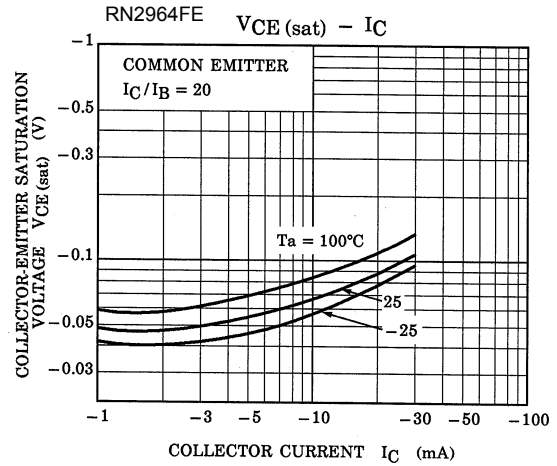
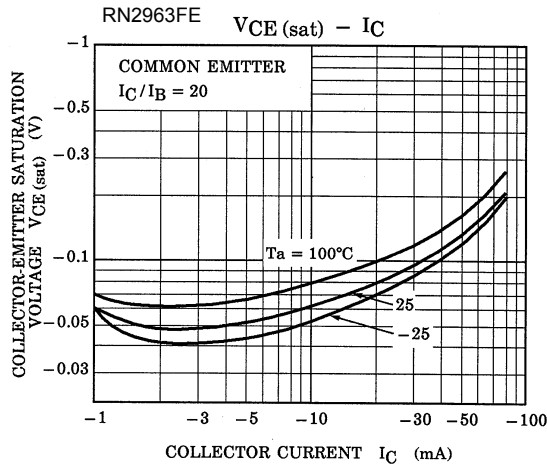
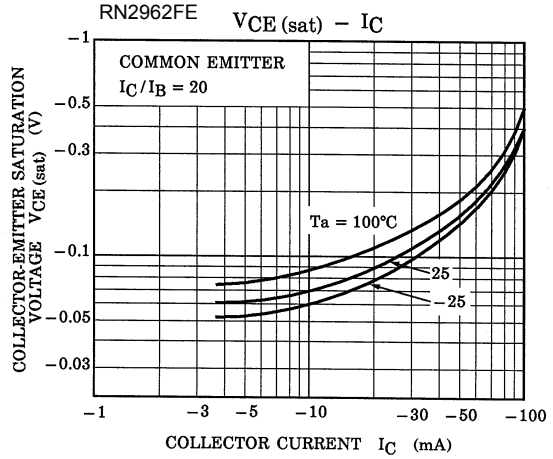
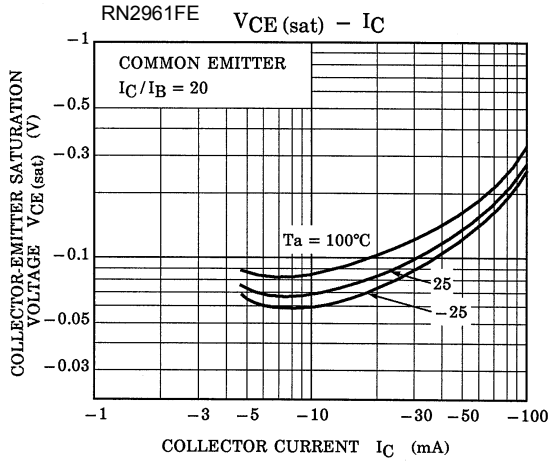
**Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)**

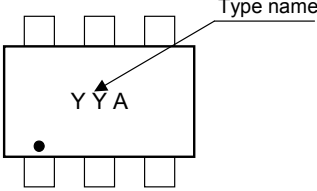
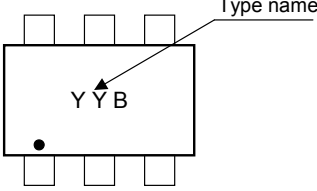
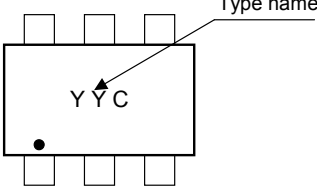
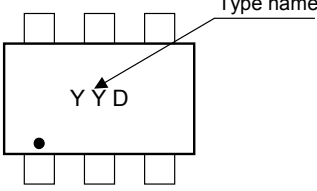
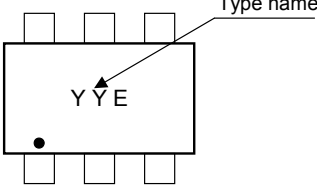
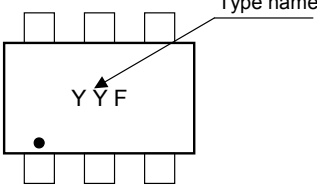
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2961FE~2966FE	$I_{CBO}$	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-100	nA
		$I_{CEO}$	$V_{CE} = -50\text{ V}, I_B = 0$	—	—	-500	
Emitter cut-off current	RN2961FE	$I_{EBO}$	$V_{EB} = -10\text{ V}, I_C = 0$	-0.82	—	-1.52	mA
	RN2962FE			-0.38	—	-0.71	
	RN2963FE			-0.17	—	-0.33	
	RN2964FE			-0.082	—	-0.15	
	RN2965FE	$V_{EB} = -5\text{ V}, I_C = 0$	-0.078	—	-0.145		
	RN2966FE		-0.074	—	-0.138		
DC current gain	RN2961FE	$h_{FE}$	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	30	—	—	
	RN2962FE			50	—	—	
	RN2963FE			70	—	—	
	RN2964FE			80	—	—	
	RN2965FE			80	—	—	
	RN2966FE			80	—	—	
Collector-emitter saturation voltage	RN2961FE~2966FE	$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	-0.1	-0.3	V
Input voltage (ON)	RN2961FE	$V_{I(ON)}$	$V_{CE} = -0.2\text{ V}, I_C = -5\text{ mA}$	-1.1	—	-2.0	V
	RN2962FE			-1.2	—	-2.4	
	RN2963FE			-1.3	—	-3.0	
	RN2964FE			-1.5	—	-5.0	
	RN2965FE			-0.6	—	-1.1	
	RN2966FE			-0.7	—	-1.3	
Input voltage (OFF)	RN2961FE~2964FE	$V_{I(OFF)}$	$V_{CE} = -5\text{ V}, I_C = -0.1\text{ mA}$	-1.0	—	-1.5	V
	RN2965FE, 2966FE			-0.5	—	-0.8	
Transition frequency	RN2961FE~2966FE	$f_T$	$V_{CE} = -10\text{ V}, I_C = -5\text{ mA}$	—	200	—	MHz
Collector output capacitance	RN2961FE~2966FE	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	3	6	pF
Input resistor	RN2961FE	R1	—	3.29	4.7	6.11	kΩ
	RN2962FE			7	10	13	
	RN2963FE			15.4	22	28.6	
	RN2964FE			32.9	47	61.1	
	RN2965FE			1.54	2.2	2.86	
	RN2966FE			3.29	4.7	6.11	
Resistor ratio	RN2961FE~2964FE	R1/R2	—	0.9	1.0	1.1	
	RN2965FE			0.0421	0.0468	0.0515	
	RN2966FE			0.09	0.1	0.11	









Type Name	Marking
RN2961FE	
RN2962FE	
RN2963FE	
RN2964FE	
RN2965FE	
RN2966FE	

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